

Title (en)

INTEGRATED CIRCUIT CONTAINING A SEMICONDUCTIVE SUBSTRATE HAVING FIELD ISOLATION REGIONS AND ELECTRICALLY CONDUCTIVE REGIONS

Publication

**EP 0068154 A3 19860507 (EN)**

Application

**EP 82104709 A 19820528**

Priority

US 27911981 A 19810630

Abstract (en)

[origin: EP0068154A2] An integrated circuit in the form of a MOSFET device contains a refractory metallic silicide (9) beneath a field isolation region (10) and in electrical contact with electrical conductive regions (P) of active impurity dopants in a semiconductive substrate (21). The layer of silicide (9) is fabricated by depositing refractory metal and reacting it with the substrate beneath by heat or ion implantation.

IPC 1-7

**H01L 21/76**; **H01L 21/74**; **H01L 23/52**

IPC 8 full level

**H01L 27/10** (2006.01); **H01L 21/3205** (2006.01); **H01L 21/331** (2006.01); **H01L 21/74** (2006.01); **H01L 21/76** (2006.01); **H01L 21/762** (2006.01); **H01L 23/52** (2006.01); **H01L 23/535** (2006.01); **H01L 29/06** (2006.01); **H01L 29/73** (2006.01); **H10B 12/00** (2023.01)

CPC (source: EP US)

**H01L 21/743** (2013.01 - EP US); **H01L 21/76202** (2013.01 - EP US); **H01L 21/76237** (2013.01 - EP US); **H01L 23/535** (2013.01 - EP US); **H01L 29/0638** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

C-Set (source: EP US)

**H01L 2924/0002** + **H01L 2924/00**

Citation (search report)

- [X] US 3659162 A 19720425 - TOSHIO WADA, et al
- [Y] US 3653120 A 19720404 - SIRRINE RICHARD C, et al
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- [A] SOLID STATE TECHNOLOGY, vol. 24, no. 1, January 1981, pages 65-72, Port Washington, , New York, US; F. MOHAMMADI: "Silicides for interconnection technology"

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Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

**EP 0068154 A2 19830105**; **EP 0068154 A3 19860507**; **EP 0068154 B1 19890308**; DE 3279523 D1 19890413; JP S587840 A 19830117; US 4446476 A 19840501

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**EP 82104709 A 19820528**; DE 3279523 T 19820528; JP 6484882 A 19820420; US 27911981 A 19810630